

# General purpose (dual digital transistors)

## EMD6 / UMD6N / IMD6A

### ●Features

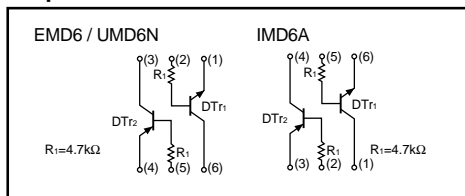
- 1) Both the DTA143T chip and DTC143T chip in an EMT or UMT or SMT package.
- 2) Mounting possible with EMT3 or UMT3 or SMT3 automatic mounting machines.
- 3) Transistor elements are independent, eliminating interference.
- 4) Mounting cost and area can be cut in half.

### ●Structure

A PNP and NPN digital transistor  
(each with a single built in resistor)

The following characteristics apply to both the DT<sub>r1</sub> and DT<sub>r2</sub>, however, the “-” sign on DT<sub>r2</sub> values for the PNP type have been omitted.

### ●Equivalent circuit



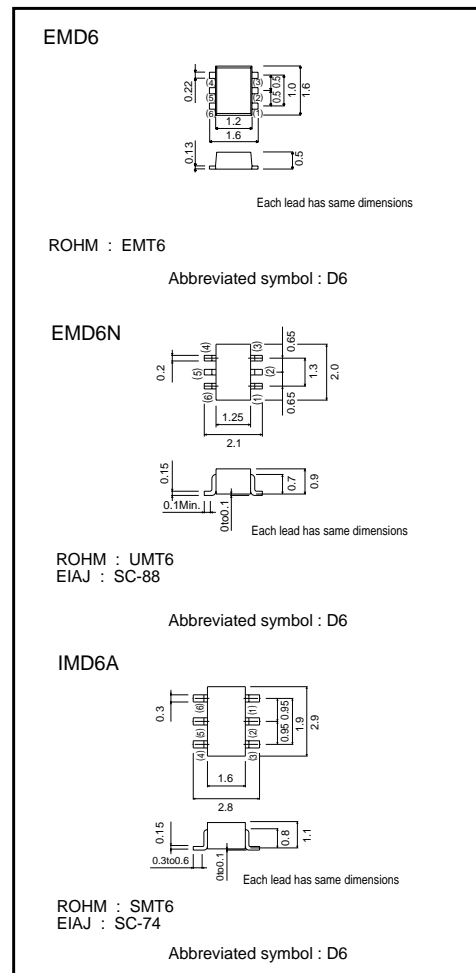
### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CBO</sub>	50	V
Collector-emitter voltage	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	100	mA
Collector power dissipation	EMD6, UMD6N	150 (TOTAL)	mW *1
	IMD6A	300 (TOTAL)	mW *2
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

\*1 120mW per element must not be exceeded.

\*2 200mW per element must not be exceeded.

### ●External dimensions (Units : mm)



Transistors

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	50	–	–	V	I <sub>c</sub> =50μA
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	50	–	–	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EB0</sub>	5	–	–	V	I <sub>E</sub> =50μA
Collector cutoff current	I <sub>CBO</sub>	–	–	0.5	μA	V <sub>CB</sub> =50V
Emitter cutoff current	I <sub>EBO</sub>	–	–	0.5	μA	V <sub>EB</sub> =4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	–	–	0.3	V	I <sub>c</sub> /I <sub>B</sub> =5mA/0.25mA
DC current transfer ratio	h <sub>FE</sub>	100	250	600	–	V <sub>CE</sub> =5V, I <sub>c</sub> =1mA
Transition frequency	f <sub>T</sub>	–	250	–	MHz	V <sub>CE</sub> =10mA, I <sub>E</sub> =-5mA, f=100MHz *
Input resistance	R <sub>1</sub>	3.29	4.7	6.11	kΩ	–

\* Transition frequency of the transistor

●Packaging specifications

Type	Package	Taping		
	Code	T2R	TR	T148
	Basic ordering unit (pieces)	8000	3000	3000
EMD6	○	—	—	—
UMD6N	—	○	—	—
IMD6A	—	—	—	○

●Electrical characteristic curves

DTr1 (NPN)

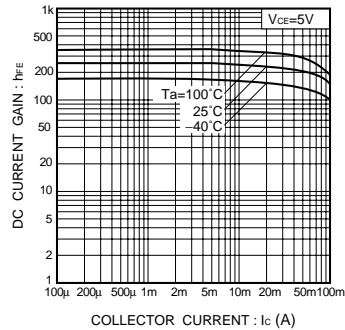


Fig.1 DC current gain vs. collector current

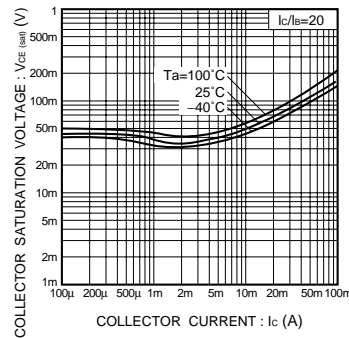


Fig.2 Collector-emitter saturation voltage vs. collector current

DTr2 (PNP)

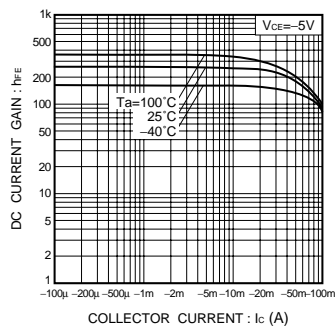


Fig.3 DC current gain vs. collector current

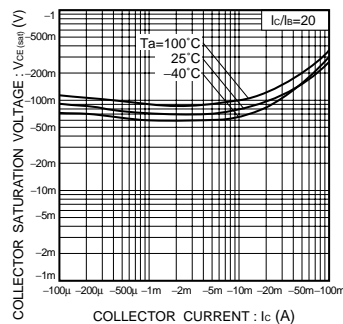


Fig.4 Collector-emitter saturation voltage vs. collector current